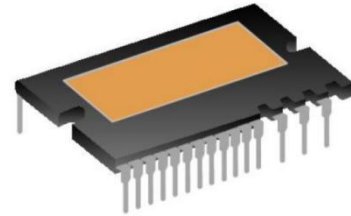


**Features:**

- 650V 10A Three-Phase IGBT inverter with control ICs inside
- Integrated OC SC protection & temperature output
- Very low thermal resistance
- High efficiency due to very low losses
- Integrated bootstrap diodes
- High reliability & strong SC withstand ability

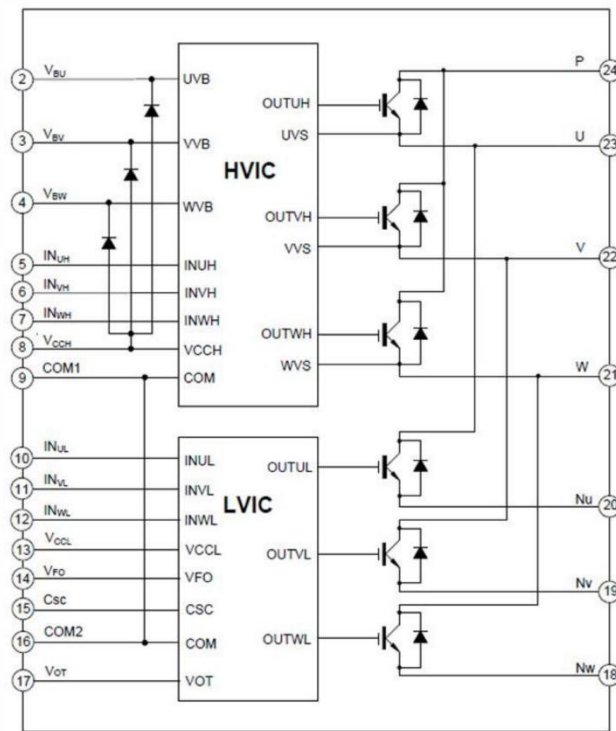
**DIP25****Applications:**

- Home appliances
- Motor drives
- General inverter

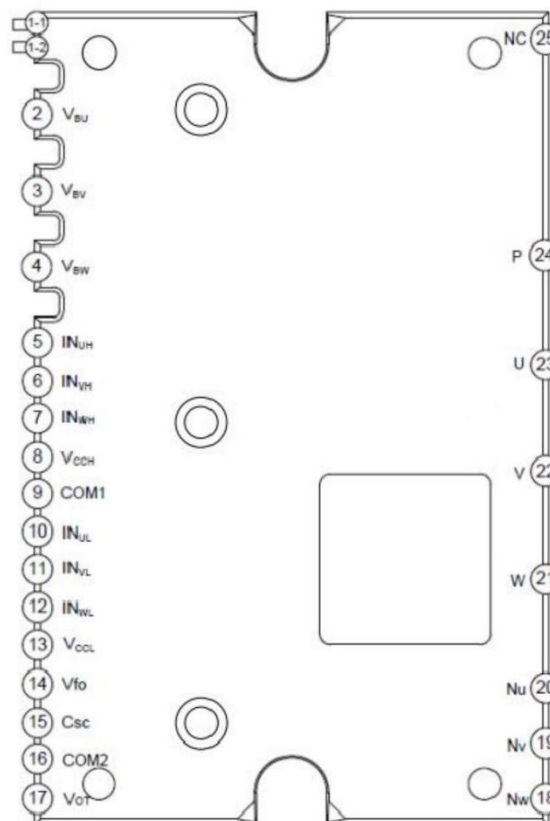
**Package parameters**

Type	Marking	Package	Packaging Method
JM10Z07DL1	JM10Z07DL1	DIP25	Tube

### Internal Electrical Schematic



### Pin Configuration



## Pin Description

Pin	Name	Descriptions
1-1	NC	No Connection
1-2	NC	No Connection
2	V <sub>BU</sub>	U-phase high side floating IC supply voltage
3	V <sub>BV</sub>	V-phase high side floating IC supply voltage
4	V <sub>BW</sub>	W-phase high side floating IC supply voltage
5	IN <sub>UH</sub>	U-phase high side gate driver input
6	IN <sub>VH</sub>	V-phase high side gate driver input
7	IN <sub>WH</sub>	W-phase high side gate driver input
8	V <sub>CCH</sub>	High side gate drive supply voltage
9	COM1	Module common ground
10	IN <sub>UL</sub>	U-phase low side gate driver input
11	IN <sub>VL</sub>	V-phase low side gate driver input
12	IN <sub>WL</sub>	W-phase low side gate driver input
13	V <sub>CCL</sub>	Low side gate drive supply voltage
14	V <sub>FO</sub>	Fault Output
15	C <sub>SC</sub>	External capacitor for short-circuit current detection input and low-pass filtering
16	COM2	Module common ground
17	V <sub>OT</sub>	Temperature output terminal
18	N <sub>W</sub>	W-phase DC negative terminal
19	N <sub>V</sub>	V-phase DC negative terminal
20	N <sub>U</sub>	U-phase DC negative terminal
21	W	Output for W Phase
22	V	Output for V Phase
23	U	Output for U Phase
24	P	Positive DC-Link Input
25	NC	No Connection

**Absolute Maximum Ratings** ( $T_{vj}=25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Values	Unit
<b>Inverter Part</b>			
$V_{PN}$	Supply voltage	450	V
$V_{PN(surge)}$	Supply voltage (surge)	500	V
$V_{CES}$	Collector – Emitter voltage	600	V
$I_C$	Each IGBT collector current, $T_C = 25^{\circ}\text{C}$ , $T_{vj} \leq 150^{\circ}\text{C}$	10	A
$I_{CP}$	Each IGBT collector current (Peak), $T_C = 25^{\circ}\text{C}$ , $T_{vj} \leq 150^{\circ}\text{C}$	20	A
$P_D$	Power dissipation per 1 chip, $T_C = 25^{\circ}\text{C}$	45	W
<b>Control Part</b>			
$V_{CC}$	Control supply voltage	20	V
$V_{BS}$	High–Side control bias voltage	20	V
$V_{IN}$	Input signal voltage	-0.3~ $V_{CC}+0.3$	V
$V_{FO}$	Fault output supply voltage	-0.3~ $V_{CC}+0.3$	V
$T_{vj}$	Operating junction temperature	-40 to 150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-40 to 150	$^{\circ}\text{C}$
$R_{thjc-IGBT}$	Single IGBT thermal resistance, junction-case	3.0	$^{\circ}\text{C}/\text{W}$
$R_{thjc-FRD}$	Single FRD thermal resistance, junction-case	3.6	$^{\circ}\text{C}/\text{W}$
VISO	Isolation test voltage (1min, RMS, $f = 60\text{Hz}$ )	1500	Vrms

**Absolute Maximum Ratings** ( $T_{vj}=25^{\circ}\text{C}$ , unless otherwise noted)

Symbol	Parameter	Values			Unit
		Min.	Typ.	Max.	
$V_{PN}$	Supply voltage	-	300	400	V
$V_{CC}$	Control supply voltage	13.2	-	20	V
$V_{BS}$	High side control voltage	13.0	-	20	V
$V_{HO}$	High side driver output voltage	$V_{SS}$	-	$V_{BS}$	V
$V_{LO}$	Low side driver output voltage	$V_{SS}$	-	$V_{CC}$	V

**Electrical Characteristics** ( $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise note)

**Inverter Part**

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$V_{CEsat}$	Collector – Emitter saturation voltage	$V_{CC}=V_{BS}=15\text{V}$ $V_{IN}=5\text{V}, I_C=10\text{A}$	-	1.8	-	V
$V_F$	FRD forward voltage	$V_{IN}=0\text{V}, I_F=10\text{A}$	-	1.4	-	V
$t_{on}$	High side switching & recovery time	$V_{PN} = 300\text{V}$ $V_{CC} = V_{BS} = 15\text{V}$ $I_C = 10\text{A}, V_{IN} = 0\text{V to } 5\text{V}$ Inductive load	-	553	-	ns
$t_r$			-	19	-	ns
$t_{off}$			-	423	-	ns
$t_f$			-	73	-	ns
$t_{rr}$			-	101	-	ns
$t_{on}$	Low side switching & recovery time	$I_C = 10\text{A}, V_{IN} = 0\text{V to } 5\text{V}$ Inductive load	-	650	-	ns
$t_r$			-	56	-	ns
$t_{off}$			-	533	-	ns
$t_f$			-	55	-	ns
$t_{rr}$			-	140	-	ns
$I_{CES}$	Collector–Emitter leakage current	$V_{CE}=600\text{V}$	-	-	10	$\mu\text{A}$

**Control Part**

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> supply current	V <sub>CC</sub> =15V, V <sub>IN</sub> =0V	-	-	1.3	mA
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	V <sub>BS</sub> =15V, V <sub>IN</sub> =0V	-	-	300	uA
V <sub>FOH</sub>	Fault output voltage	V <sub>SC</sub> =0V V <sub>FO</sub> Circuit: 10kΩ to 5V	4.9	-	-	V
V <sub>FOL</sub>		V <sub>SC</sub> =1V, I <sub>FO</sub> =1mA	-	-	0.95	V
t <sub>FO</sub>	Fault output pulse width	Fault duration	40	-	200	us
V <sub>SC(ref)</sub>	Short-circuit trip level	V <sub>CC</sub> =15V	0.455	0.48	0.505	V
OT <sub>t</sub>	Over temperature protection trip	LVIC temperature	100	120	140	°C
OT <sub>th</sub>	Over temperature protection hysteresis	LVIC temperature Hysteresis	-	10	-	°C
V <sub>OT</sub>	Temperature output	LVIC temperature=25°C	1.06	1.2	1.39	V
		LVIC temperature=90°C	2.63	2.77	2.91	V
UV <sub>CCt</sub>	Low side undervoltage protection	Trip level	9.0	10.0	11.0	V
UV <sub>CCr</sub>		Reset level	10.0	11.0	12.0	V
UV <sub>BSt</sub>	High side undervoltage protection	Trip level	9.0	10.0	11.0	V
UV <sub>BSr</sub>		Reset level	10.0	11.0	12.0	V
V <sub>IH</sub>	On threshold voltage	Applied among inputs and COM	-	-	2.5	V
V <sub>IL</sub>	Off threshold voltage		0.8	-	-	V

## Temperature Output Function Description

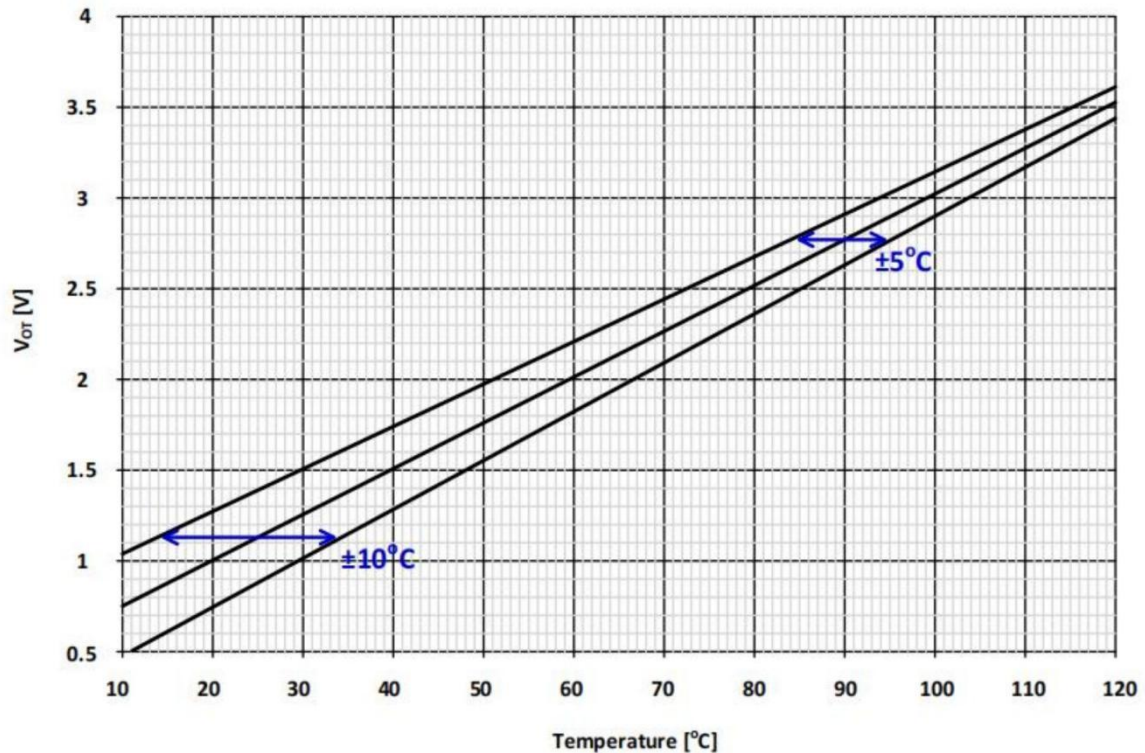


Figure 1.  $V_{OT}$  temperature characteristics

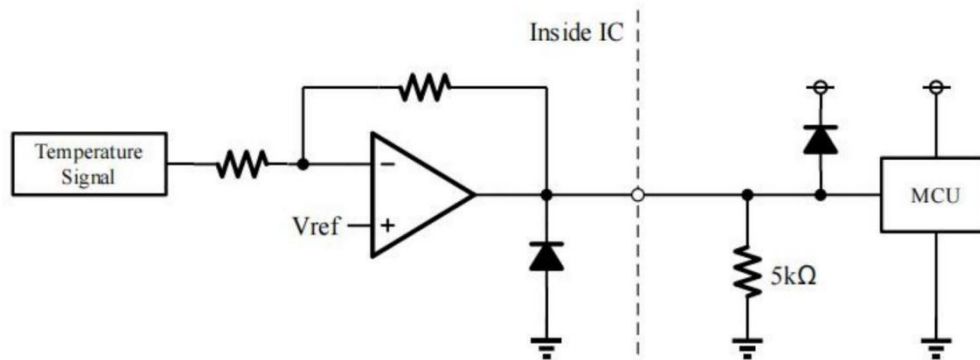
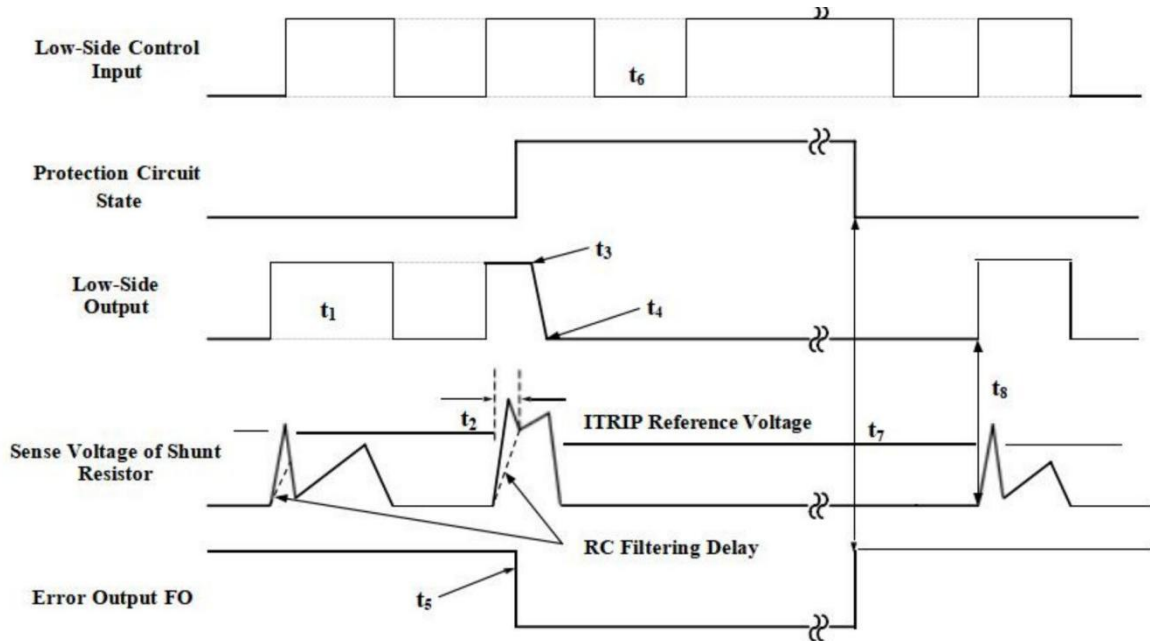


Figure 2.  $V_{OT}$  output circuit

(1) Connect 5kΩ to VOT pin if temperature monitoring function is used, and then the internal OTP function is omitted. Leave the VOT pin open (no connect) if internal over-temperature shutdown function is used. However, the VOT is also operated, but with inferior accuracy.

(2) In the case of using VOT with low voltage controller like 3.3V MCU, VOT output might exceed control supply voltage 3.3V when temperature rises excessively. If system use slow voltage controller, it is recommended to insert a clamp diode between control supply of the controller and  $V_{OT}$  output for preventing over voltage destruction.

## Short-Circuit Protection Function Description



**Figure 2. Short-circuit protection**

t1 : Normal operation, Low-Side output.

t2 : Short circuit current detection ( $I_{TRIP}$  trigger).

(It is recommended to set RC time constant 1.5-2.0 $\mu s$  so that IGBT shunt down within 2.0 $\mu s$  when  $I_{TRIP}$  be triggered.) t3 : All low-side outputs are hard interrupted.

t4 : All low-side outputs turn off.

t5 : FO outputs for  $t_{FO}=40\mu s$  (min).

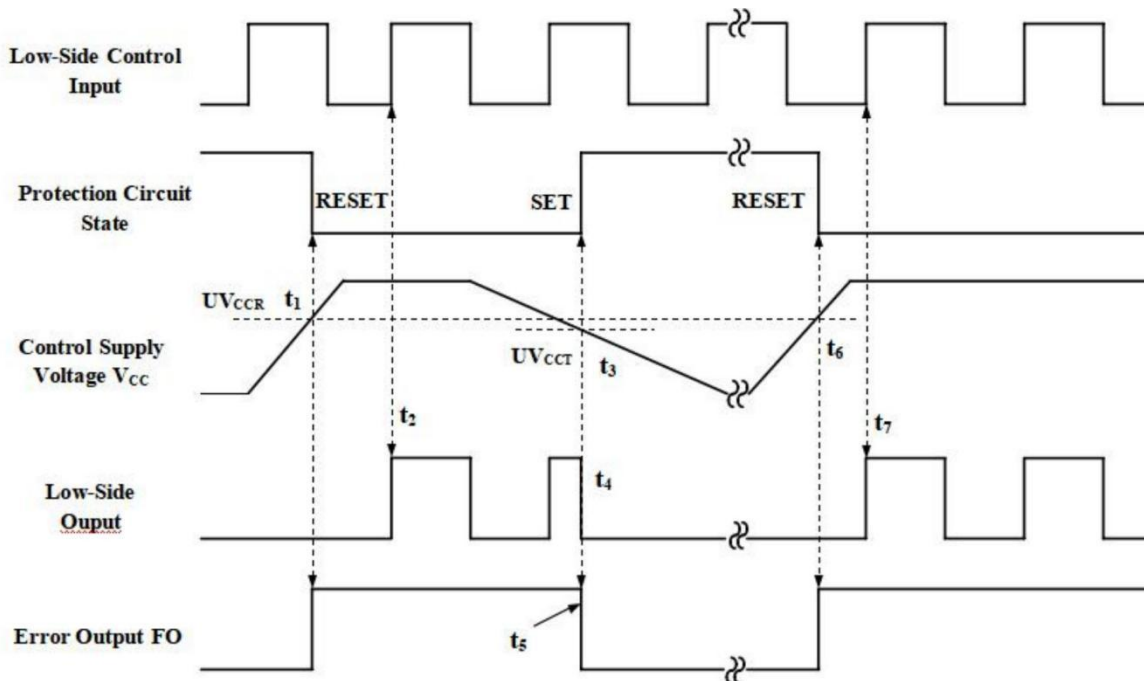
t6 : Input is low, outputs turn off.

t7 : FO rise to high, but outputs don't turn on until input signal change low to high.

t8 : Normal operation, outputs on.



## Low-side Under-Voltage Protection Description



**Figure 3. Under-voltage protection(low side)**

t1 : Control supply voltage  $V_{CC}$  exceeds under voltage reset level ( $UV_{CCR}$ ), but output turns on until next high level signal.

t2 : Normal operation, outputs turn on.

t3 :  $V_{CC}$  level drops to under voltage trip level. ( $UV_{CCR}$ )

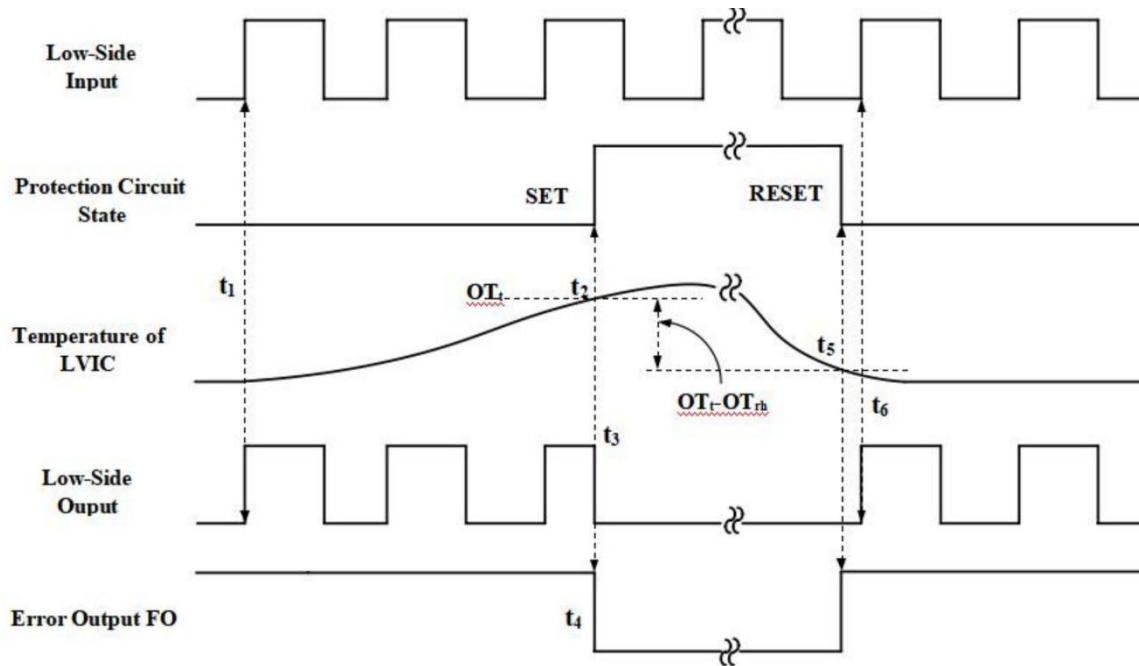
t4 : All low side outputs turn off in spite of control input condition.

t5 : FO outputs for  $t_{FO}=40\mu s$  (Min), but output is extended during  $V_{CC}$  keeps below  $UV_{CCR}$ .

t6 :  $V_{CC}$  level reaches  $UV_{CCR}$ .

t7 : Normal operation, outputs turn on.

## Over Temperature Protection Description



**Figure 4. Over temperature protection**

t1 : Normal operation, low side outputs turn on.

t2 : LVIC temperature exceeds over temperature trip level (OTt).

t3 : All low side outputs turn off in spite of control input condition.

t4 : FO outputs for  $t_{FO}=40\mu s$  (Min), but output is extended during LVIC temperature higher than OTt.

t5 : LVIC temperature drops to over temperature reset level.

t6 : Normal operation, low side outputs turn on by next high level signal.



## Revision history

Date	Revision	Changes
2025-01-10	Rev 1.0	Release of the preliminary datasheet.

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